

ADVANCED POWER TECHNOLOGY T-39-15

APT6060AN 600V 11.5A 0.60 Ω
APT5560AN 550V 11.5A 0.60 Ω
APT6070AN 600V 10.5A 0.70 Ω
APT5570AN 550V 10.5A 0.70 Ω

POWER MOS IV™

N - CHANNEL ENHANCEMENT MODE HIGH VOLTAGE POWER MOSFETS

MAXIMUM RATINGS

All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Parameter	APT 5560AN	APT 6060AN	APT 5570AN	APT 6070AN	UNIT
V_{DSS}	Drain-Source Voltage	550	600	550	600	Volts
I_D	Continuous Drain Current	11.5		10.5		Amps
I_{DM}	Pulsed Drain Current[1]	46		42		Amps
V_{GS}	Gate-Source Voltage	±30				Volts
P_D	Total Power Dissipation @ T_C = 25°C, Derate Above 25°C	198				Watts
T_J,T_{STG}	Operating and Storage Junction Temperature Range	- 55 to 150				°C

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number		MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage (V_{GS} = 0V, I_D = 250 µA)	APT6060AN / APT6070AN	600			Volts
		APT5560AN / APT5570AN	550			Volts
I_{DSS}	Zero Gate Voltage Drain Current (V_{DS} = V_{DSS}, V_{GS} = 0V)				250	µA
	(V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125°C)				1000	
I_{GSS}	Gate-Source Leakage Current (V_{GS} = ±30V, V_{DS} = 0V)				±100	nA
I_D(ON)	On State Drain Current [2] (V_{DS} > I_D(ON) x R_{DS}(ON) Max, V_{GS} = 10V)	APT6060AN / APT5560AN	11.5			Amps
		APT6070AN / APT5570AN	10.5			Amps
V_{GS}(TH)	Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 1mA)		2		4	Volts
R_{DS}(ON)	Static Drain-Source On-State Resistance [2] (V_{GS} = 10V, I_D = 0.5 I_D [Cont.])	APT6060AN / APT5560AN			0.60	Ohms
		APT6070AN / APT5570AN			0.70	Ohms

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.63	°C/W
$R_{\theta JA}$	Junction to Ambient			30	°C/W
T_L	Max. Lead Temp. for Soldering Conditions: 0.063" from Case for 10 Sec.			300	°C

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DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1 MHz		1510	1800	pF
C_{oss}	Output Capacitance			280	390	pF
C_{rss}	Reverse Transfer Capacitance			105	157	pF
Q_g	Total Gate Charge [3]	V_{GS} = 10V, I_D = I_D [Cont.] V_{DD} = 0.5 V_{DSS}		66	105	nC
Q_{gs}	Gate-Source Charge			8	12	nC
Q_{gd}	Gate-Drain ("Miller") Charge			35	53	nC
t_d(on)	Turn-on Delay Time	V_{DD} = 0.5 V_{DSS} I_D = I_D [Cont.], V_{GS} = 15V R_G = 1.8Ω		13	25	ns
t_r	Rise Time			18	35	ns
t_d(off)	Turn-off Delay Time			51	77	ns
t_f	Fall Time			21	41	ns

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number		MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)	**APT6060AN / APT5560AN**			11.5	Amps
		APT6070AN / APT5570AN			10.5	Amps
I_{SM}	Pulsed Source Current[1] (Body Diode)	**APT6060AN / APT5560AN**			46	Amps
		APT6070AN / APT5570AN			42	Amps
V_{SD}	Diode Forward Voltage[2] (V_{GS} = 0V, I_S = -I_D [Cont.])				1.3	Volts
t_{rr}	Reverse Recovery Time (I_S = -I_D [Cont.], dI_S/dt = 100A/μs)		148	297	594	ns
Q_{rr}	Reverse Recovery Charge		2	4	8	μC

SAFE OPERATING AREA CHARACTERISTICS

Symbol	Characteristic	Test Conditions / Part Number	MIN	TYP	MAX	UNIT
SOA1	Safe Operating Area	V_{DS} = 0.4 V_{DSS}, I_{DS} = P_D / 0.4 V_{DSS}, t = 1 Sec.	198			Watts
SOA2	Safe Operating Area	I_{DS} = I_D [Cont.], V_{DS} = P_D / I_D [Cont.], t = 1 Sec.	198			Watts
I_{LM}	Inductive Current Clamped	**APT6060AN / APT5560AN**	46			Amps
		APT6070AN / APT5570AN	42			Amps

1.) Repetitive Rating: Pulse width limited by maximum junction temperature. See Transient Thermal Impedance Curve. (Fig.1)

2.) Pulse Test: Pulse width < 380 μS
Duty Cycle < 2%

3.) See MIL-STD-750 Method 3471

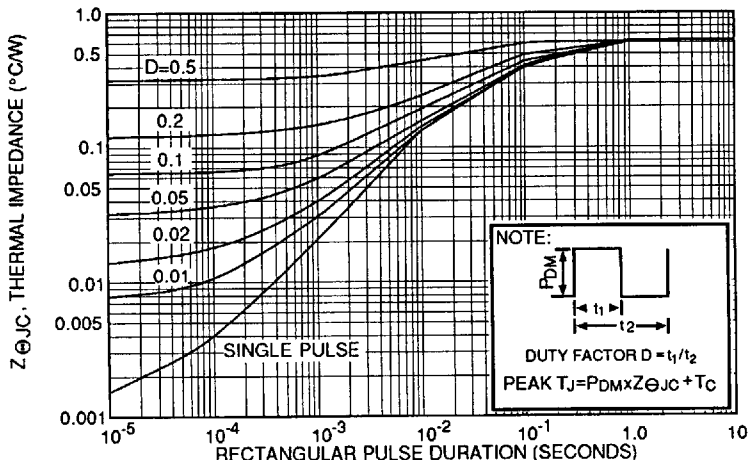


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

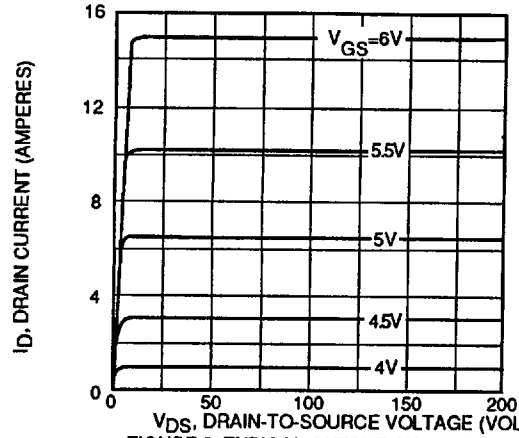


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

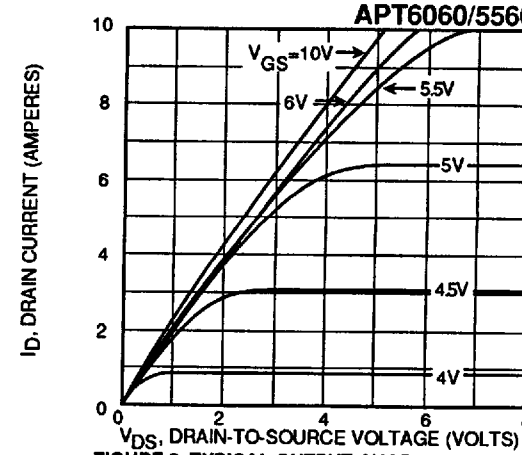


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

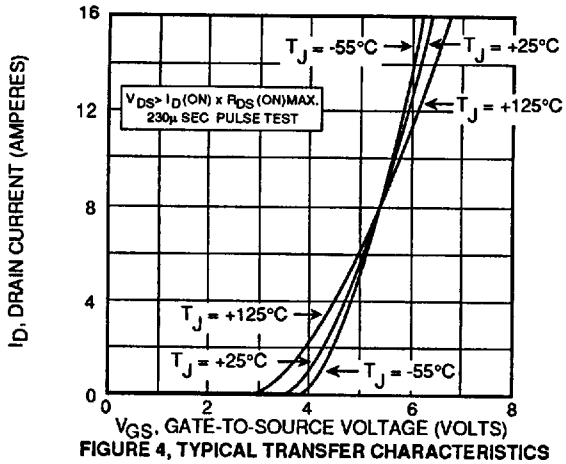


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

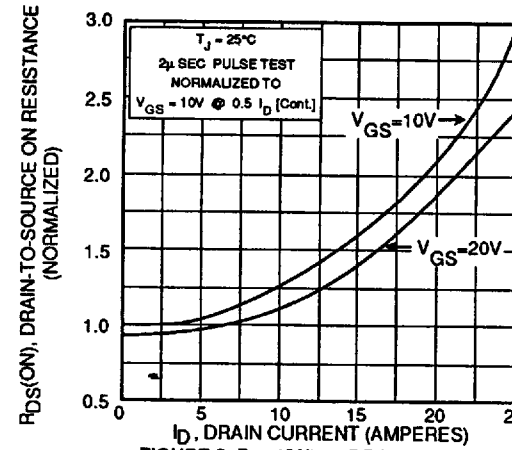


FIGURE 5, $R_{DS(ON)}$ vs DRAIN CURRENT

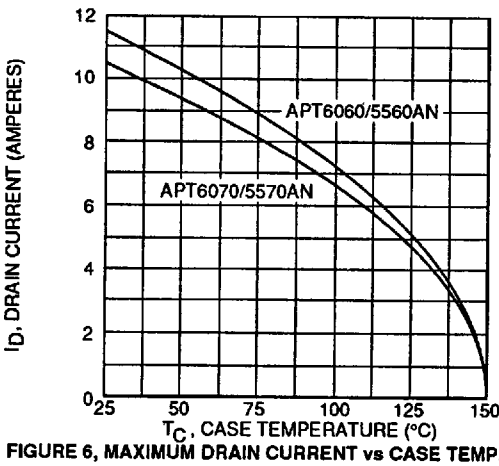


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

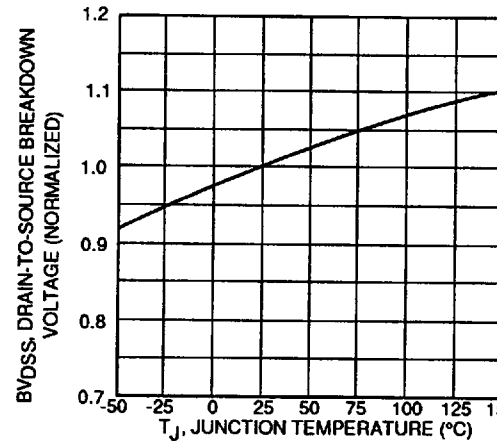


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

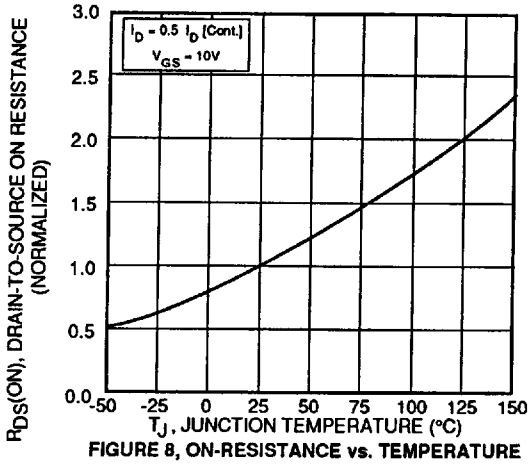


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

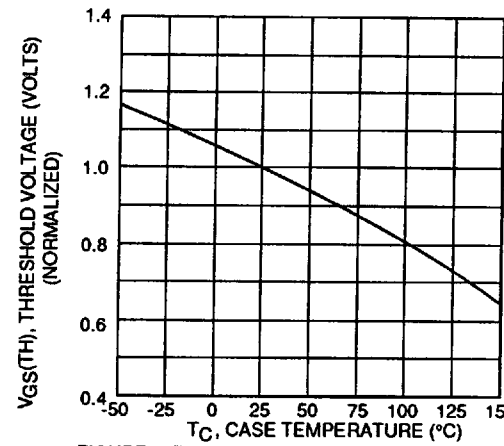


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

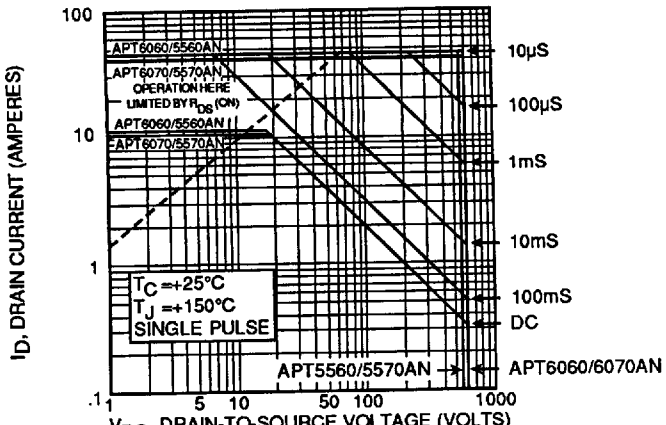


FIGURE 10, MAXIMUM SAFE OPERATING AREA

T-39-15

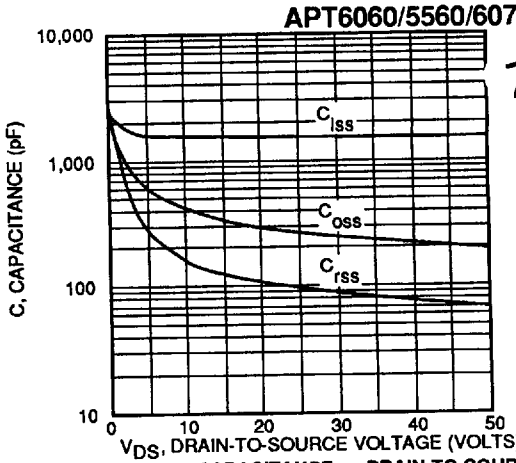


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

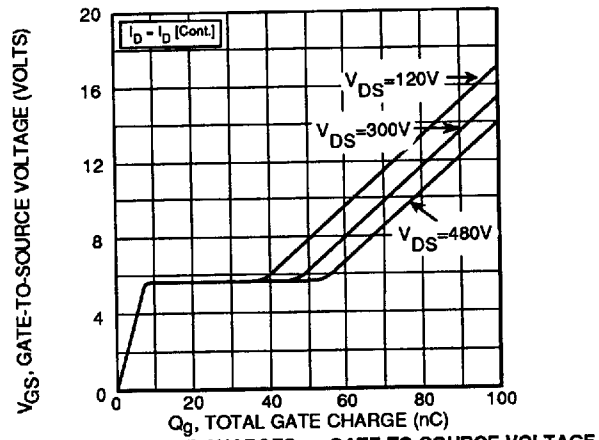


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

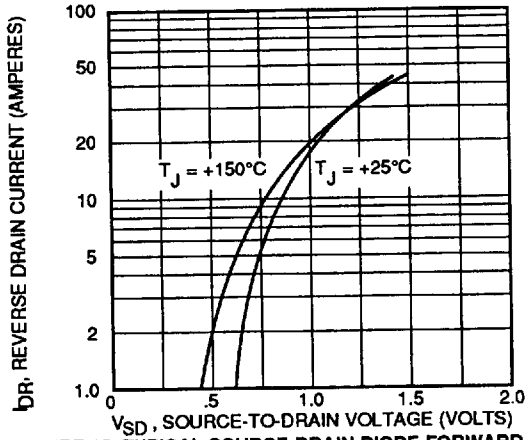
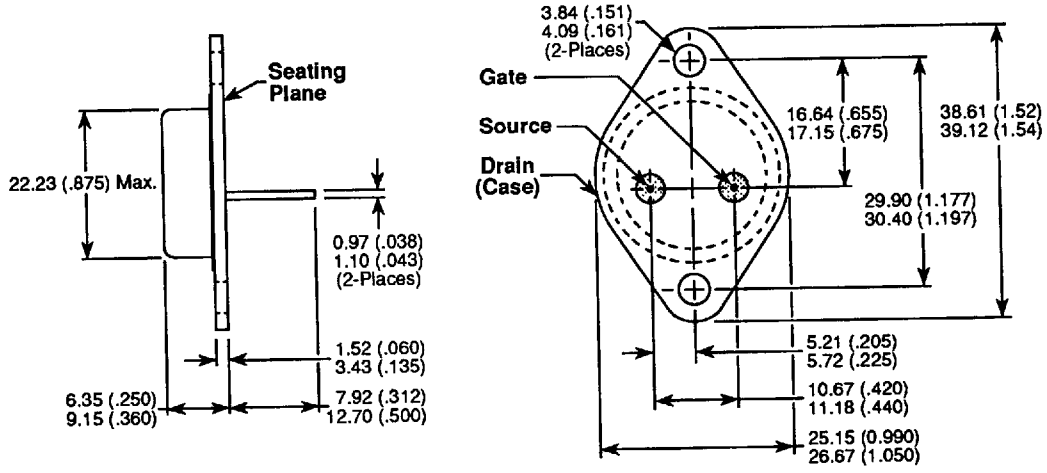


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

TO-3 Package Outline (TO-204AA)



Dimensions in Millimeters and (Inches)

050-6003
Rev-